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Adams

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[54] **METHOD OF SPIRAL RESIST DEPOSITION**

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[21] Appl. No.: **118,538**

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118/52; 437/231

[58] Field of Search **437/229, 231; 427/240;**

118/52

[57] ABSTRACT

A method of depositing a material upon a substrate is disclosed. A material, such as photoresist, is deposited upon a substrate such as a semiconductor wafer by spinning the substrate and commencing deposition at the edge of the wafer and moving inward in a spiral pattern. The method produces a more uniform coating than hitherto available.

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7 Claims, 3 Drawing Sheets

